

BIPOLAR ANALOG INTEGRATED CIRCUIT

μ**PC2734GR**

L-BAND DOWN-CONVERTER IC

DESCRIPTION

The μ PC2734GR is a silicon monolithic IC designed for L band down-converter. This IC consists of double balanced mixer (DBM), local oscillator, local oscillation buffer amplifier, IF amplifier, buffer amplifier for SAW filter and voltage regulator.

The package is 20-pin SSOP suitable for high-density surface mount.

The μ PC2734GR is manufactured using NEC's 20 GHz fr NESATTM III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

FEATURES

- Wide band operation fRF = 0.9 to 2.1 GHz
- Dual IF outputs for BS and CS Band.
- Single-end push-pull IF amplifier suppresses fluctuation of output impedance.
- Supply voltage : 5 V
- Packaged in 20-pin SSOP suitable for high-density mounting.

★ APPLICATION

• L-Band receiver (0.9 to 2.1 GHz)

ORDERING INFORMATION

Part Number	Package	Supplying Form
μPC2734GR-E1	20-pin Plastic SSOP (5.72mm (225 mil))	Embossed tape 12 mm wide. Pin 1 indicates pull-out direction of tape. Qty 2.5 kp/reel.

Remark To order evaluation samples, please contact your local NEC sales office.

(Part number for sample order: µPC2734GR)

Caution electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

INTERNAL BLOCK DIAGRAM AND PIN CONFIGURATION



PIN FUNCTIONS

Pin No.	Pin Name	Pin Voltage TYP. (V)	Function and Explanation	Equivalent Circuit
1	MIX. OUT1	4.2	Mixer output pin for IF band pass filter.	
2	GND	0.0	GND pin of mixer, IF amplifier, and regulator switch.	
3	MIX. IN2	2.4	RF signal input pin. In case of single input, 3 pin or 4 pin should be grounded through capacitor.	
4	MIX. IN1	2.4		
5 6 7	NC		Non Connection.	
8	Vcc	5.0	Power supply pin of mixer, IF amplifier, and regulator switch.	
9	IF OUT1	3.1	IF output pin. If switch pin is open or less than 2 volt (TYP.), signal comes through.	9, 10
10	IF OUT2	3.1	IF output pin. If switch pin is more than 3 volt (TYP.), signal comes through.	
11	SW	2.0	Switching pin of IF output1 or IF output2 pin.	
12	Vcc	5.0	Power supply pin of buffer amplifier and oscillator amplifier.	

Pin No.	Pin Name	Pin Voltage TYP. (V)	Function and Explanation	Equivalent Circuit
13	OSC OUT	3.4	Oscillator output pin.	
14	GND	0.0	GND pin of buffer amplifier and oscillator amplifier.	
15	OSC C1	5.0	Loads should be connected to collector pin.	17 15 18 16
16	OSC B2	2.9	Base pin of oscillator. Grounded through capacitor.	
17	OSC B1	2.9	Base pin of oscillator. Assemble LC resonator with 18 pin through capacitor to oscillate with active feedback loop.	
18	OSC C2	5.0	Loads should be connected to collector pin.	
19	GND	0.0	GND pin of mixer, IF amplifier, regulator switch.	
20	MIX. OUT2	4.2	Mixer output pin for IF band pass filter.	

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Ratings	Unit
Supply Voltage	Vcc	T _A = +25 °C	6.0	V
Power Dissipation	PD	T _A = +85 °C ^{Note}	430	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		-55 to +150	°C

Note Mounted on $50 \times 50 \times 1.6$ mm double copper epoxy glass board.

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc	4.5	5.0	5.5	V
Operating Ambient Temperature	Та	-40	+25	+85	°C

ELECTRICAL CHARACTERISTICS (TA = +25 $^{\circ}$ C, Vcc = 5 V, ^{Note})

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	lcc	no input signal	28	40	52	mA
Lower Input Frequency	frF1		_	-	0.9	GHz
Upper Input Frequency	frf2		2.1	_	_	GHz
Conversion Gain 1	CG1	$f_{RF} = 0.9 \text{ GHz}, P_{in} = -30 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	10.0	13.0	16.0	dB
Conversion Gain 2	CG2	$f_{RF} = 2.1 \text{ GHz}, P_{in} = -30 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	7.5	10.5	13.5	dB
Conversion Gain 3	CG3	$f_{RF} = 0.9 \text{ GHz}, P_{in} = -30 \text{ dBm}, f_{IF} = 479.5 \text{ MHz}$	9.0	12.0	15.0	dB
Conversion Gain 4	CG4	$f_{RF} = 2.1 \text{ GHz}, P_{in} = -30 \text{ dBm}, f_{IF} = 479.5 \text{ MHz}$	7.0	10.0	13.0	dB
Noise Figure 1	NF1	frf = 0.9 GHz, fif = 402.8 MHz	-	9.0	12.0	dB
Noise Figure 2	NF2	frf = 2.1 GHz, fif = 402.8 MHz	-	14.0	17.0	dB
Noise Figure 3	NF3	frf = 0.9 GHz, fif = 479.5 MHz	-	10.0	13.0	dB
Noise Figure 4	NF4	frf = 2.1 GHz, fif = 479.5 MHz	-	15.0	18.0	dB
Saturated Output Power 1	Po(sat)1	$f_{RF} = 0.9 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	1.0	4.0	_	dBm
Saturated Output Power 2	Po(sat)2	$f_{RF} = 2.1 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	1.0	4.0	_	dBm
Saturated Output Power 3	Po(SAT)3	$f_{RF} = 0.9 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 479.5 \text{ MHz}$	0.5	3.5	_	dBm
Saturated Output Power 4	Po(sat)4	fref = 2.1 GHz, Pin = 0 dBm, fif = 479.5 MHz	0.0	3.0	_	dBm
3rd Order Intermodulation Distortion 1	IM31	frF = 0.9, 0.93 GHz, Pin = -25 dBm	_	47	_	dBc
3rd Order Intermodulation Distortion 2	IM32	frf = 2.1, 2.13 GHz, Pin = -25 dBm	_	49	_	dBc

Note By measurement circuit

STANDARD CHARACTERISTICS (REFERENCE VALUES) (TA = +25 $^{\circ}$ C, Vcc = 5 V, ^{Note})

Parameter	Symbol	Test Conditions		Reference Values		
Falameter			MIN.	TYP.	MAX.	Unit
Lower Input Frequency	frf1		_	_	0.9	GHz
Upper Input Frequency	frf2		2.1	_	_	GHz
Conversion Gain 1	CG1	f_{RF} = 0.9 GHz, P_{in} = -30 dBm, f_{IF} = 402.8 MHz	_	14.0	_	dB
Conversion Gain 2	CG2	f_{RF} = 2.1 GHz, P_{in} = -30 dBm, f_{IF} = 402.8 MHz	_	14.5	_	dB
Conversion Gain 3	CG3	$f_{RF} = 0.9 \text{ GHz}, P_{in} = -30 \text{ dBm}, f_{IF} = 479.5 \text{ MHz}$	_	13.5	-	dB
Conversion Gain 4	CG4	f_{RF} = 2.1 GHz, P_{in} = -30 dBm, f_{IF} = 479.5 MHz	_	14.0	-	dB
Noise Figure 1	NF1	$f_{RF} = 0.9 \text{ GHz}, P_{in} = -30 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	_	9.7	-	dB
Noise Figure 2	NF2	f_{RF} = 2.1 GHz, P_{in} = -30 dBm, f_{IF} = 402.8 MHz	_	11.0	-	dB
Noise Figure 3	NF3	f_{RF} = 0.9 GHz, P_{in} = -30 dBm, f_{IF} = 479.5 MHz	-	9.7	-	dB
Noise Figure 4	NF4	f_{RF} = 2.1 GHz, P_{in} = -30 dBm, f_{IF} = 479.5 MHz	_	11.0	-	dB
Saturated Output Power 1	Po(SAT)1	$f_{RF} = 0.9 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	-	5.0	-	dBm
Saturated Output Power 2	Po(SAT)2	$f_{RF} = 2.1 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 402.8 \text{ MHz}$	-	5.0	-	dBm
Saturated Output Power 3	Po(sat)3	$f_{RF} = 0.9 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 479.5 \text{ MHz}$	_	4.0	-	dBm
Saturated Output Power 4	Po(sat)4	$f_{RF} = 2.1 \text{ GHz}, P_{in} = 0 \text{ dBm}, f_{IF} = 479.5 \text{ MHz}$	_	5.5	-	dBm
3rd Order Intermodulation Distortion 1	IM31	frF = 0.9, 0.93 GHz, Pin = -25 dBm	_	44	-	dBc
3rd Order Intermodulation Distortion 2	IM32	frF = 2.1, 2.13 GHz, Pin = -25 dBm	_	43	-	dBc

Note By application circuit

TYPICAL CHARACTERISTICS (TA = +25 °C) - on Measurement Circuit -











STANDARD CHARACTERISTICS (TA = +25 °C) - on Application Circuit -



OSC Frequency fosc (GHz)

Remark The graphs indicate nominal characteristics.



MEASUREMENT CIRCUIT



APPLICATION CIRCUIT EXAMPLE



The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

Illustration of the application circuit assembled on evaluation board



- C1:150pF
- C2:3300pF
- C3:1000pF
- C4 : 2pF
- C5 : 1pF
- C6: 4pF Note assembled on the back side
- R1 : $1M\Omega$
- R2 : 150Ω
- L1, L2:

L3



★ PACKAGE DIMENSIONS

20 PIN PLASTIC SSOP (5.72 mm(225)) (UNIT: mm)







RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235°C or below Time: 30 seconds or less (at 210°C) Count: 3, Exposure limit: None ^{Note}	IR35-00-3
VPS	Package peak temperature: 215°C or below Time: 40 seconds or less (at 200°C) Count: 3, Exposure limit: None ^{Note}	VP15-00-3
Wave Soldering	Soldering bath temperature: 260°C or below Time: 10 seconds or less Count: 1, Exposure limit: None ^{Note}	WS60-00-1
Partial Heating	Pin temperature: 300°C Time: 3 seconds or less (per side of device) Exposure limit: None ^{Note}	_

Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).



NESAT (NEC Silicon Advanced Technology) is a trademark of NEC Corporation.

- The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
- No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.
- NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.
- Descriptions of circuits, software, and other related information in this document are provided for illustrative purposes in semiconductor product operation and application examples. The incorporation of these circuits, software, and information in the design of the customer's equipment shall be done under the full responsibility of the customer. NEC Corporation assumes no responsibility for any losses incurred by the customer or third parties arising from the use of these circuits, software, and information.
- While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.
- NEC devices are classified into the following three quality grades:
 "Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a
 customer designated "quality assurance program" for a specific application. The recommended applications of
 a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device
 before using it in a particular application.
 - Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - Specific: Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

M7 98.8